Low-power buffer/line driver; 3-state Rev. 6 — 2 October 2015

Product data sheet

#### **General description** 1.

The 74AUP1G126 provides a single non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (OE). A LOW level at pin OE causes the output to assume a high-impedance OFF-state. This device has the input-disable feature, which allows floating input signals. The inputs are disabled when the output enable input OE is LOW.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire  $V_{CC}$  range from 0.8 V to 3.6 V. This device ensures a very low static and dynamic power consumption across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I<sub>OFF</sub>. The I<sub>OFF</sub> circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

#### **Features and benefits** 2.

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
  - JESD8-12 (0.8 V to 1.3 V)
  - JESD8-11 (0.9 V to 1.65 V)
  - JESD8-7 (1.2 V to 1.95 V)
  - JESD8-5 (1.8 V to 2.7 V)
  - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
  - HBM JESD22-A114F Class 3A exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption;  $I_{CC} = 0.9 \,\mu A$  (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V<sub>CC</sub>
- Input-disable feature allows floating input conditions
- I<sub>OFF</sub> circuitry provides partial power-down mode operation
- Multiple package options
- Specified from –40 °C to +85 °C and –40 °C to +125 °C



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#### **Ordering information** 3.

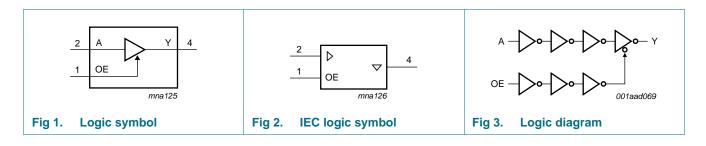
Table 1. Ordering	g information			
Type number	Package			
	Temperature range	Name	Description	Version
74AUP1G126GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74AUP1G126GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1.45 $\times$ 0.5 mm	SOT886
74AUP1G126GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1 $\times$ 0.5 mm	SOT891
74AUP1G126GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115
74AUP1G126GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202
74AUP1G126GX	–40 °C to +125 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body $0.8 \times 0.8 \times 0.35$ mm	SOT1226

#### Marking 4.

Table 2. Marking	
Type number	Marking code <sup>[1]</sup>
74AUP1G126GW	pN
74AUP1G126GM	pN
74AUP1G126GF	pN
74AUP1G126GN	рN
74AUP1G126GS	рN
74AUP1G126GX	pN

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

#### **Functional diagram** 5.

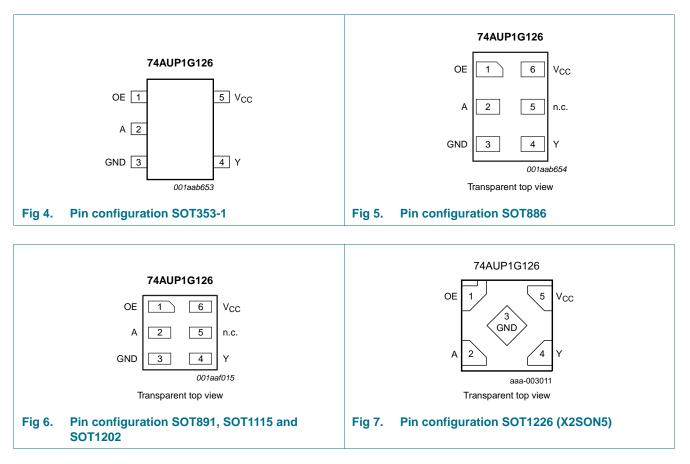


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#### **Pinning information** 6.

### 6.1 Pinning



### 6.2 Pin description

Symbol	Pin		Description
	TSSOP5 and X2SON5	XSON6	
OE	1	1	output enable input
A	2	2	data input
GND	3	3	ground (0 V)
Y	4	4	data output
n.c.	-	5	not connected
V <sub>CC</sub>	5	6	supply voltage

#### **Functional description** 7.

Input		Output
OE	A	Y
н	L	L
Н	Н	Н
L	Х	Z

[1] H = HIGH voltage level;

L = LOW voltage level;

X = Don't care;

Z = high-impedance OFF-state.

#### 8. **Limiting values**

#### Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>1</sub> < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
Ι <sub>ΟΚ</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
Vo	output voltage	Active mode	<u>[1]</u> –0.5	$V_{CC} + 0.5$	V
		Power-down mode	<u>[1]</u> –0.5	+4.6	V
Ι <sub>Ο</sub>	output current	$V_{O} = 0 V$ to $V_{CC}$	-	±20	mA
I <sub>CC</sub>	supply current		-	+50	mA
I <sub>GND</sub>	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb}$ = -40 °C to +125 °C	[2] _	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

For TSSOP5 packages: above 87.5 °C the value of Ptot derates linearly with 4.0 mW/K. [2] For XSON6 and X2SON5 packages: above 118 °C the value of Ptot derates linearly with 7.8 mW/K.

#### **Recommended operating conditions** 9.

Table 6.	Recommended operating conditi	ons			
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V <sub>CC</sub>	V
		Power-down mode; $V_{CC} = 0 V$	0	3.6	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 V \text{ to } 3.6 V$	0	200	ns/V

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## **10. Static characteristics**

### Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = 2	5 °C					
VIH	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70 \times V_{\text{CC}}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC}$ = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
VIL	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30\times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
/ <sub>ОН</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_O$ = –20 $\mu\text{A};~V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
		$I_0 = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_0 = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
/ <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_O$ = 20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.3\times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_0$ = 1.9 mA; $V_{CC}$ = 1.65 V	-	-	0.31	V
		$I_{O}$ = 2.3 mA; $V_{CC}$ = 2.3 V	-	-	0.31	V
		$I_{O}$ = 3.1 mA; $V_{CC}$ = 2.3 V	-	-	0.44	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
I	input leakage current	$V_I$ = GND to 3.6 V; $V_{CC}$ = 0 V to 3.6 V	-	-	±0.1	μΑ
OZ	OFF-state output current		-	-	±0.1	μA
OFF	power-off leakage current	$V_{I} \text{ or } V_{O}$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.2	μΑ
\I <sub>OFF</sub>	additional power-off leakage current	$      V_1 \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V}; \\       V_{CC} = 0 \text{ V to } 0.2 \text{ V} $	-	-	±0.2	μΑ
сс	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = 0 \ A; \\ V_{CC} = 0.8 \ V \ \text{to} \ 3.6 \ V \end{array}$	-	-	0.5	μA

### Low-power buffer/line driver; 3-state

#### Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

- <b>,</b>	Parameter	Conditions	Min	Тур	Max	Unit
∆l <sub>CC</sub>	additional supply current	data input; V <sub>I</sub> = V <sub>CC</sub> – 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 3.3 V	<u>[1]</u> -	-	40	μA
		OE input; V <sub>I</sub> = V <sub>CC</sub> – 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 3.3 V	<u>[1]</u> -	-	110	μA
		all inputs; V <sub>I</sub> = GND to 3.6 V; OE = GND; V <sub>CC</sub> = 0.8 V to 3.6 V	[2] -	-	1	μA
CI	input capacitance	$V_{CC}$ = 0 V to 3.6 V; $V_{I}$ = GND or $V_{CC}$	-	0.9	-	pF
Co	output capacitance	output enabled; $V_O = GND$ ; $V_{CC} = 0 V$	-	1.7	-	pF
		output disabled; V <sub>CC</sub> = 0 V to 3.6 V; V <sub>O</sub> = GND or V <sub>CC</sub>	-	1.5	-	pF
T <sub>amb</sub> = -4	40 °C to +85 °C					
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70\times V_{CC}$	-	-	V
		$V_{CC}$ = 0.9 V to 1.95 V	$0.65\times V_{CC}$	-	-	V
		$V_{CC}$ = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 V \text{ to } 3.6 V$	2.0	-	-	V
VIL	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30\times V_{CC}$	V
		$V_{CC}$ = 0.9 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC}$ = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
/ <sub>ОН</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = –20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O}$ = -2.3 mA; $V_{CC}$ = 2.3 V	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = 20 $\mu A;$ $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		$I_{O} = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3\times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.35	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
I	input leakage current	$V_{\rm I}$ = GND to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.5	μΑ
OZ	OFF-state output current		-	-	±0.5	μA
OFF	power-off leakage current	$V_{\rm I}~{\rm or}~V_{\rm O}$ = 0 V to 3.6 V; $V_{\rm CC}$ = 0 V	-	-	±0.5	μΑ

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$\Delta I_{OFF}$	additional power-off leakage current	$V_{I}$ or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V		-	-	±0.6	μΑ
СС	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$		-	-	0.9	μA
∆l <sub>CC</sub>	additional supply current	data input; V <sub>I</sub> = V <sub>CC</sub> – 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 3.3 V	<u>[1]</u>	-	-	50	μA
		OE input; V <sub>I</sub> = V <sub>CC</sub> – 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 3.3 V	<u>[1]</u>	-	-	120	μA
		all inputs; V <sub>I</sub> = GND to 3.6 V; OE = GND; V <sub>CC</sub> = 0.8 V to 3.6 V	<u>[2]</u>	-	-	1	μA
T <sub>amb</sub> = -	40 °C to +125 °C						
VIH	HIGH-level input voltage	$V_{CC} = 0.8 V$		$0.75 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V		$0.70\times V_{CC}$	-	-	V
		$V_{CC}$ = 2.3 V to 2.7 V		1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		2.0	-	-	V
/ <sub>IL</sub> LOW	LOW-level input voltage	$V_{CC} = 0.8 V$		-	-	$0.25\times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V		-	-	$0.30\times V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		-	-	0.9	V
V <sub>OH</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$					
		$I_{O}$ = -20 $\mu$ A; V <sub>CC</sub> = 0.8 V to 3.6 V		V <sub>CC</sub> - 0.11	-	-	V
		$I_0 = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$		$0.6 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$		0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$		1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$		1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$		1.67	-	-	V
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$		2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$		2.30	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$					
		$I_{O}$ = 20 $\mu$ A; $V_{CC}$ = 0.8 V to 3.6 V		-	-	0.11	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V		-	-	$0.33 \times V_{CC}$	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V		-	-	0.41	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V		-	-	0.39	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$		-	-	0.36	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V		-	-	0.50	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$		-	-	0.36	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$		-	-	0.50	V
	input leakage current	$V_{I} = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V		-	-	±0.75	μA
l <sub>oz</sub>	OFF-state output current	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{O} = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 3.6 \text{ V}$		-	-	±0.75	μA
I <sub>OFF</sub>	power-off leakage current	$V_{\rm I}$ or $V_{\rm O} = 0$ V to 3.6 V; $V_{\rm CC} = 0$ V		-	-	±0.75	μA

### Table 7. Static characteristics ...continued

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### Low-power buffer/line driver; 3-state

At recom	mended operating conditions	s; voltages are referenced to GND (grour	nd = 0 V).			
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$\Delta I_{OFF}$	additional power-off leakage current	$V_1$ or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
I <sub>CC</sub>	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = O \ A; \\ V_{CC} = 0.8 \ V \ to \ 3.6 \ V \end{array}$	-	-	1.4	μΑ
$\Delta I_{CC}$	additional supply current	data input; V_I = V_{CC} - 0.6 V; I_O = 0 A; V_{CC} = 3.3 V	<u>[1]</u> _	-	75	μΑ
		OE input; V <sub>I</sub> = V <sub>CC</sub> – 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 3.3 V	<u>[1]</u> _	-	180	μΑ
		all inputs; V <sub>I</sub> = GND to 3.6 V; OE = GND; V <sub>CC</sub> = 0.8 V to 3.6 V	[2] _	-	1	μΑ

#### Table 7. Static characteristics ... continued

[1] One input at  $V_{CC}$  – 0.6 V, other input at  $V_{CC}$  or GND.

[2] To show  $I_{CC}$  remains very low when the input-disable feature is enabled.

## **11. Dynamic characteristics**

#### Table 8. **Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 10

Symbol	Parameter	Conditions		Min	Typ 1	Мах	Unit
T <sub>amb</sub> = 25	°C; C <sub>L</sub> = 5 pF						
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	[2]				
		$V_{CC} = 0.8 V$		-	20.6	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		2.8	5.5	10.5	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		2.2	3.9	6.1	ns
		$V_{CC}$ = 1.65 V to 1.95 V		1.9	3.2	4.8	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.6	2.6	3.6	ns
		$V_{CC}$ = 3.0 V to 3.6 V		1.4	2.4	3.1	ns
t <sub>en</sub>	enable time	OE to Y; see Figure 9	[3]				
		$V_{CC} = 0.8 V$		-	71.6	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		2.8	6.2	12.4	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		2.3	4.2	6.9	ns
		$V_{CC}$ = 1.65 V to 1.95 V		1.9	3.3	5.3	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.5	2.4	3.6	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		1.3	2.0	2.9	ns
t <sub>dis</sub>	disable time	OE to Y; see Figure 9	[4]				
		$V_{CC} = 0.8 V$		-	10.3	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		2.6	4.2	6.2	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		2.1	3.2	4.4	ns
		$V_{CC}$ = 1.65 V to 1.95 V		2.1	3.1	4.4	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.7	2.4	3.2	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.1	2.8	3.6	ns

### Low-power buffer/line driver; 3-state

Symbol	Parameter	Conditions		Min	Typ <mark>[1]</mark>	Мах	Unit
T <sub>amb</sub> = 25	°C; C <sub>L</sub> = 10 pF						
t <sub>pd</sub>	propagation delay	see Figure 8	[2]				
		$V_{CC} = 0.8 V$		-	24.0	-	ns
		$V_{CC}$ = 1.1 V to 1.3 V		3.2	6.4	12.3	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.1	4.5	7.3	ns
		$V_{CC}$ = 1.65 V to 1.95 V		1.9	3.8	5.5	ns
		$V_{CC}$ = 2.3 V to 2.7 V		2.1	3.2	4.2	ns
		$V_{CC}$ = 3.0 V to 3.6 V		1.8	3.0	3.8	ns
t <sub>en</sub>	enable time	see Figure 9	<u>[3]</u>				
		$V_{CC} = 0.8 V$		-	75.3	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.2	7.1	14.1	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.2	4.8	8.0	ns
		$V_{CC}$ = 1.65 V to 1.95 V		1.8	3.9	5.9	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.5	2.9	4.2	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		1.4	2.6	3.6	ns
t <sub>dis</sub>	disable time	see Figure 9	[4]				
		$V_{CC} = 0.8 V$		-	12.2	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.5	5.3	7.6	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		2.2	4.1	5.6	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.4	4.2	5.7	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.9	3.2	4.1	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		2.4	4.1	5.0	ns
T <sub>amb</sub> = 25	°C; C <sub>L</sub> = 15 pF						
t <sub>pd</sub>	propagation delay	see Figure 8	[2]				
		$V_{CC} = 0.8 V$		-	27.4	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.6	7.2	14.1	ns
		$V_{CC} = 1.4 \text{ V}$ to 1.6 V		3.0	5.1	8.1	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V		2.2	4.3	6.3	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.0	3.7	4.9	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		2.0	3.5	4.4	ns
t <sub>en</sub>	enable time	see Figure 9	[3]				
		V <sub>CC</sub> = 0.8 V		-	79.2	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V		3.6	7.8	15.8	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V		3.0	5.4	8.8	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V		2.1	4.3	6.7	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.8	3.4	4.8	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.6	3.1	4.3	ns

#### Table 8. Dynamic characteristics ... continued

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Low-power buffer/line driver; 3-state

Symbol	Parameter	Conditions		Min	Typ <mark>[1]</mark>	Мах	Unit
t <sub>dis</sub>	disable time	see Figure 9	[4]				
		$V_{CC} = 0.8 V$		-	14.9	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		4.3	6.4	8.5	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		3.0	5.0	6.6	ns
		$V_{CC}$ = 1.65 V to 1.95 V		3.1	5.4	6.6	ns
		$V_{CC}$ = 2.3 V to 2.7 V		2.4	4.0	5.0	ns
		$V_{CC}$ = 3.0 V to 3.6 V		3.2	5.3	6.2	ns
T <sub>amb</sub> = 25	°C; C <sub>L</sub> = 30 pF						
t <sub>pd</sub>	propagation delay	see Figure 8	[2]				
		$V_{CC} = 0.8 V$		-	37.4	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		4.8	9.5	18.7	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		4.0	6.7	10.8	ns
		$V_{CC}$ = 1.65 V to 1.95 V		2.9	5.6	8.4	ns
		$V_{CC}$ = 2.3 V to 2.7 V		2.7	4.8	6.3	ns
		$V_{CC}$ = 3.0 V to 3.6 V		2.7	4.6	5.8	ns
t <sub>en</sub>	enable time	see Figure 9	<u>[3]</u>				
		$V_{CC} = 0.8 V$		-	90.6	-	ns
		$V_{CC}$ = 1.1 V to 1.3 V		4.7	10.0	20.4	ns
		$V_{CC}$ = 1.4 V to 1.6 V		3.0	6.9	11.3	ns
		$V_{CC}$ = 1.65 V to 1.95 V		2.6	5.6	8.6	ns
		$V_{CC}$ = 2.3 V to 2.7 V		2.3	4.5	6.3	ns
		$V_{CC}$ = 3.0 V to 3.6 V		2.2	4.2	5.8	ns
t <sub>dis</sub>	disable time	see Figure 9	[4]				
		$V_{CC} = 0.8 V$		-	51.6	-	ns
		$V_{CC}$ = 1.1 V to 1.3 V		6.0	9.8	13.6	ns
		$V_{CC}$ = 1.4 V to 1.6 V		4.5	7.7	10.5	ns
		$V_{CC}$ = 1.65 V to 1.95 V		5.2	8.8	11.4	ns
		$V_{\rm CC}$ = 2.3 V to 2.7 V		3.9	6.4	7.4	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		5.5	9.0	10.7	ns

#### Table 8 Dynamic characteristics ... continued

#### Low-power buffer/line driver; 3-state

Symbol	Parameter	Conditions		Min	Typ 🚹	Мах	Unit
T <sub>amb</sub> = 25	<b>°C</b>						
C <sub>PD</sub>	power dissipation capacitance	f = 1 MHz; $V_I$ = GND to $V_{CC}$	<u>[5]</u>				
		output enabled					
	$V_{CC} = 0.8 V$		-	2.7	-	pF	
		$V_{CC}$ = 1.1 V to 1.3 V		-	2.8	-	pF
		$V_{CC}$ = 1.4 V to 1.6 V		-	2.9	-	pF
		$V_{CC}$ = 1.65 V to 1.95 V		-	3.0	-	pF
	$V_{CC}$ = 2.3 V to 2.7 V		-	3.6	-	pF	
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		-	4.2	-	pF

#### Dynamic characteristics ... continued Table 8.

[1] All typical values are measured at nominal V<sub>CC</sub>.

[2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[3]  $t_{en}$  is the same as  $t_{PZH}$  and  $t_{PZL}$ .

[4]  $t_{dis}$  is the same as  $t_{PHZ}$  and  $t_{PLZ}$ .

[5]  $C_{PD}$  is used to determine the dynamic power dissipation (P<sub>D</sub> in  $\mu$ W).  $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$  $f_i$  = input frequency in MHz;  $f_o = output frequency in MHz;$  $C_L$  = output load capacitance in pF; V<sub>CC</sub> = supply voltage in V; N = number of inputs switching;  $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

#### Table 9. **Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 10

Symbol	Parameter	Conditions		–40 °C t	o +85 °C	–40 °C to +125 °C		Unit
				Min	Max	Min	Max	
C <sub>L</sub> = 5 pF								
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	<u>[1]</u>					
		$V_{CC}$ = 1.1 V to 1.3 V		2.5	11.7	2.5	12.9	ns
		$V_{CC} = 1.4 \text{ V}$ to 1.6 V		2.0	7.3	2.0	8.1	ns
		$V_{CC}$ = 1.65 V to 1.95 V		1.7	6.1	1.7	6.7	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.4	4.3	1.4	4.9	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		1.2	3.9	1.2	4.4	ns
t <sub>en</sub>	enable time	OE to Y; see Figure 9	[2]					
		$V_{CC}$ = 1.1 V to 1.3 V		2.6	13.6	2.6	13.6	ns
		$V_{CC}$ = 1.4 V to 1.6 V		2.2	7.4	2.2	7.7	ns
		$V_{CC}$ = 1.65 V to 1.95 V		1.7	5.9	1.7	6.2	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.4	3.8	1.4	4.1	ns
		$V_{CC}$ = 3.0 V to 3.6 V		1.2	3.2	1.2	3.4	ns

### Low-power buffer/line driver; 3-state

Symbol Parameter		Conditions		–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Max	Min	Мах	
t <sub>dis</sub>	disable time	OE to Y; see Figure 9	[3]					
		$V_{CC}$ = 1.1 V to 1.3 V		2.9	6.4	2.9	6.5	ns
		$V_{CC}$ = 1.4 V to 1.6 V		2.2	4.6	2.2	4.7	ns
		$V_{CC}$ = 1.65 V to 1.95 V		1.7	4.6	1.7	4.8	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.4	3.4	1.4	3.6	ns
		$V_{CC}$ = 3.0 V to 3.6 V		1.2	3.7	1.2	3.8	ns
C <sub>L</sub> = 10 p	F							
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	[1]					
		$V_{CC}$ = 1.1 V to 1.3 V		3.0	13.8	3.0	15.2	ns
		$V_{CC}$ = 1.4 V to 1.6 V		1.9	8.5	1.9	9.4	ns
		$V_{CC}$ = 1.65 V to 1.95 V		1.7	6.8	1.7	7.6	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.6	5.3	1.6	5.9	ns
		$V_{CC}$ = 3.0 V to 3.6 V		1.6	4.6	1.6	5.2	ns
t <sub>en</sub>	enable time	OE to Y; see Figure 9	[2]					
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.0	15.4	3.0	15.4	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		2.1	8.3	2.1	8.6	ns
		$V_{CC}$ = 1.65 V to 1.95 V		1.7	6.5	1.7	6.8	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.4	4.5	1.4	4.8	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		1.3	3.8	1.3	4.0	ns
t <sub>dis</sub>	disable time	OE to Y; see Figure 9	[3]					
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.3	7.9	3.3	7.9	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		2.1	5.7	2.1	5.9	ns
		$V_{CC}$ = 1.65 V to 1.95 V		1.7	5.8	1.7	6.0	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.4	4.3	1.4	4.5	ns
		$V_{CC}$ = 3.0 V to 3.6 V		1.3	5.2	1.3	5.3	ns
C <sub>L</sub> = 15 p	F							
t <sub>pd</sub>	propagation delay	A to Y; see Figure 8	<u>[1]</u>					
		$V_{CC}$ = 1.1 V to 1.3 V		3.3	15.8	3.3	17.5	ns
		$V_{CC}$ = 1.4 V to 1.6 V		2.5	9.8	2.5	10.9	ns
		$V_{CC}$ = 1.65 V to 1.95 V		2.0	7.9	2.0	8.8	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.8	6.0	1.8	6.7	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.8	5.4	1.8	6.1	ns
en	enable time	OE to Y; see Figure 9	[2]					
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.3	17.1	3.3	17.1	ns
		$V_{CC}$ = 1.4 V to 1.6 V		2.9	9.4	2.9	9.7	ns
		$V_{CC}$ = 1.65 V to 1.95 V		2.0	7.3	2.0	7.7	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.7	5.2	1.7	5.6	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		1.5	4.5	1.5	4.7	ns

#### Table 9. Dynamic characteristics ... continued

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### Low-power buffer/line driver; 3-state

Symbol	Parameter	Conditions		<b>−40 °C</b> t	to +85 °C	–40 °C to +125 °C		Unit
				Min	Max	Min	Max	
dis	disable time	OE to Y; see Figure 9	[3]			1		
		$V_{CC}$ = 1.1 V to 1.3 V		3.7	9.3	3.7	9.4	ns
		$V_{CC}$ = 1.4 V to 1.6 V		2.5	6.9	2.5	7.0	ns
		$V_{CC}$ = 1.65 V to 1.95 V		2.0	7.4	2.0	7.5	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.7	5.1	1.7	5.5	ns
		$V_{CC}$ = 3.0 V to 3.6 V		1.5	6.7	1.5	6.9	ns
C <sub>L</sub> = 30 p	F							
t <sub>pd</sub> propagation delay		A to Y; see Figure 8	<u>[1]</u>					
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		4.4	21.4	4.4	24.0	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		3.0	13.0	3.0	14.5	ns
		$V_{CC}$ = 1.65 V to 1.95 V		2.6	10.3	2.6	11.5	ns
	$V_{CC}$ = 2.3 V to 2.7 V		2.5	7.8	2.5	8.7	ns	
		$V_{CC}$ = 3.0 V to 3.6 V		2.5	7.0	2.5	8.3	ns
en	enable time	OE to Y; see Figure 9	[2]					
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		4.3	22.0	4.3	22.0	ns
		$V_{CC}$ = 1.4 V to 1.6 V		3.7	12.0	3.7	12.5	ns
		$V_{CC}$ = 1.65 V to 1.95 V		3.2	9.5	3.2	10.1	ns
		$V_{CC}$ = 2.3 V to 2.7 V		2.9	6.8	2.9	7.3	ns
		$V_{CC}$ = 3.0 V to 3.6 V		2.7	6.4	2.7	6.7	ns
dis	disable time	OE to Y; see Figure 9	[3]					
		$V_{CC}$ = 1.1 V to 1.3 V		4.7	14.3	4.7	14.4	ns
		$V_{CC}$ = 1.4 V to 1.6 V		3.0	10.7	3.0	11.0	ns
		$V_{CC}$ = 1.65 V to 1.95 V		2.6	11.5	2.6	11.6	ns
		$V_{CC}$ = 2.3 V to 2.7 V		2.3	9.0	2.3	10.2	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.2	10.8	2.2	12.0	ns

### Table 9. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 10</u>

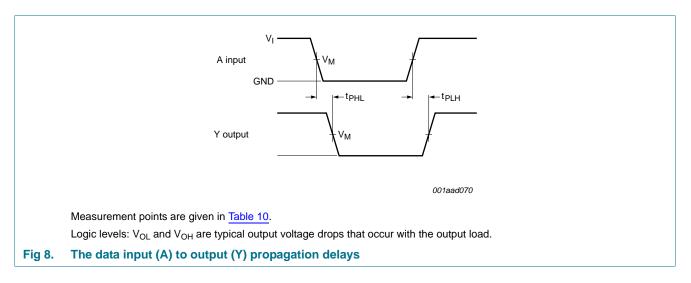
[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[2]  $t_{en}$  is the same as  $t_{PZH}$  and  $t_{PZL}$ .

[3]  $t_{dis}$  is the same as  $t_{PHZ}$  and  $t_{PLZ}$ .

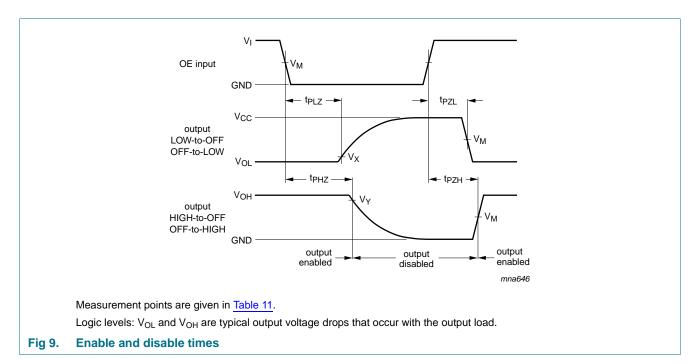
#### Low-power buffer/line driver; 3-state

### 12. Waveforms



#### Table 10. Measurement points

Supply voltage	Output	Input		
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>	VI	$t_r = t_f$
0.8 V to 3.6 V	$0.5  imes V_{CC}$	$0.5\times V_{CC}$	V <sub>CC</sub>	≤ 3.0 ns



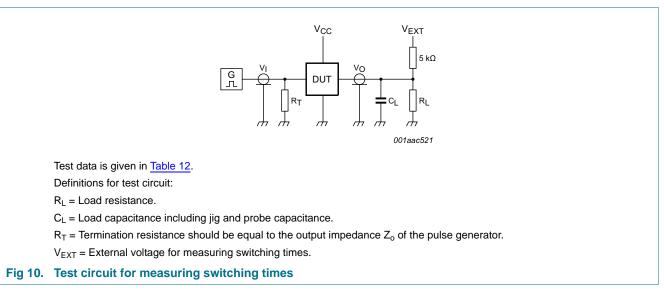
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### Low-power buffer/line driver; 3-state

Table 11. Measureme	ent points			
Supply voltage	Input	Output		
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>	V <sub>X</sub>	V <sub>Y</sub>
0.8 V to 1.6 V	$0.5\times V_{CC}$	$0.5\times V_{CC}$	$V_{OL} + 0.1 V$	V <sub>OH</sub> – 0.1 V
1.65 V to 2.7 V	$0.5\times V_{CC}$	$0.5\times V_{CC}$	$V_{OL} + 0.15 \ V$	V <sub>OH</sub> – 0.15 V
3.0 V to 3.6 V	$0.5\times V_{CC}$	$0.5\times V_{CC}$	$V_{OL} + 0.3 V$	V <sub>OH</sub> – 0.3 V



#### Table 12. Test data

Supply voltage	Load		V <sub>EXT</sub>		
V <sub>cc</sub>	CL	R <sub>L</sub> [1]	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k $\Omega$ or 1 M $\Omega$	open	GND	$2 \times V_{CC}$

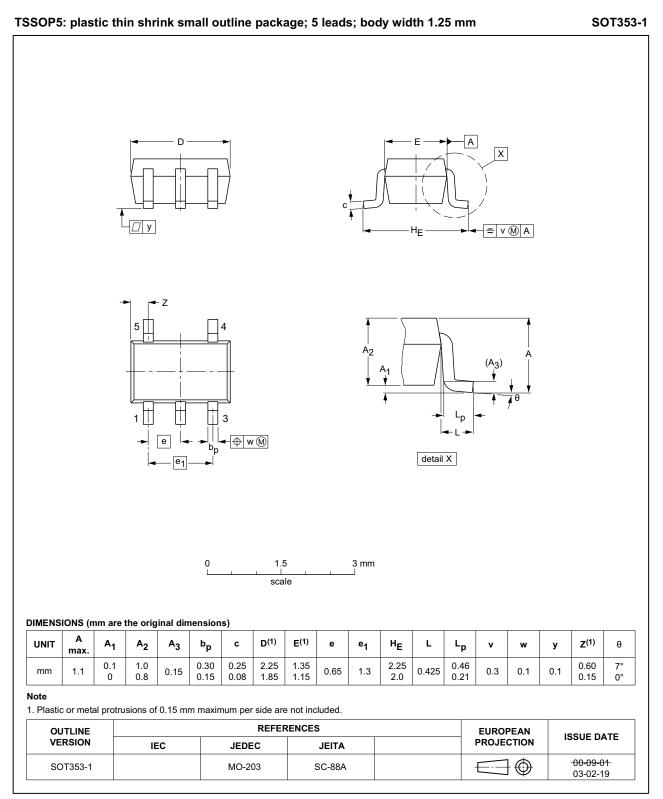
[1] For measuring enable and disable times  $R_L = 5 k\Omega$ , for measuring propagation delays, setup and hold times and pulse width  $R_L = 1 M\Omega$ .

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Low-power buffer/line driver; 3-state

### 13. Package outline



### Fig 11. Package outline SOT353-1 (TSSOP5)

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Low-power buffer/line driver; 3-state

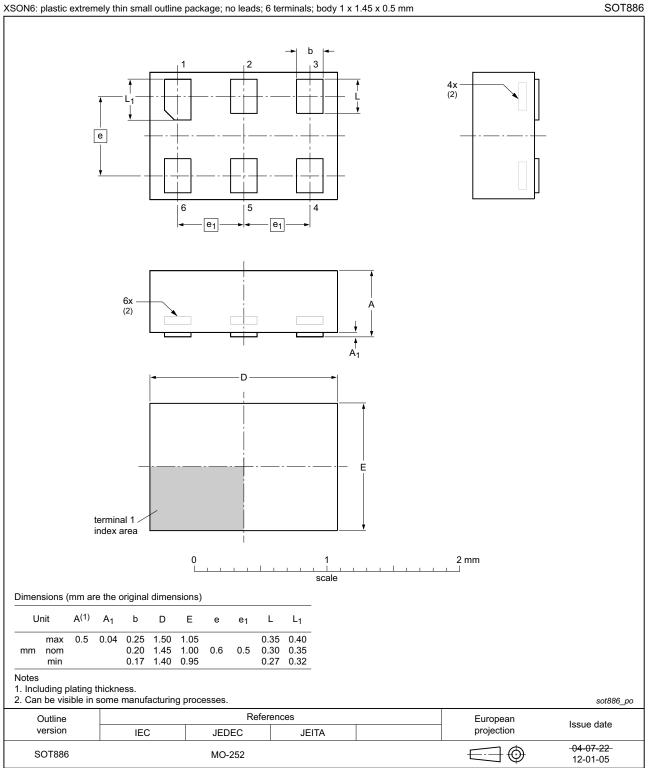


Fig 12. Package outline SOT886 (XSON6)

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Low-power buffer/line driver; 3-state

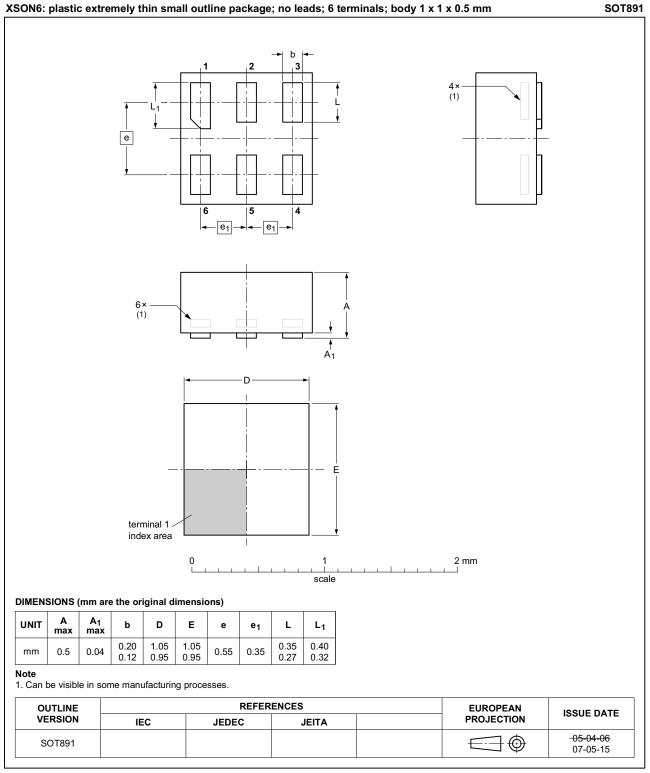
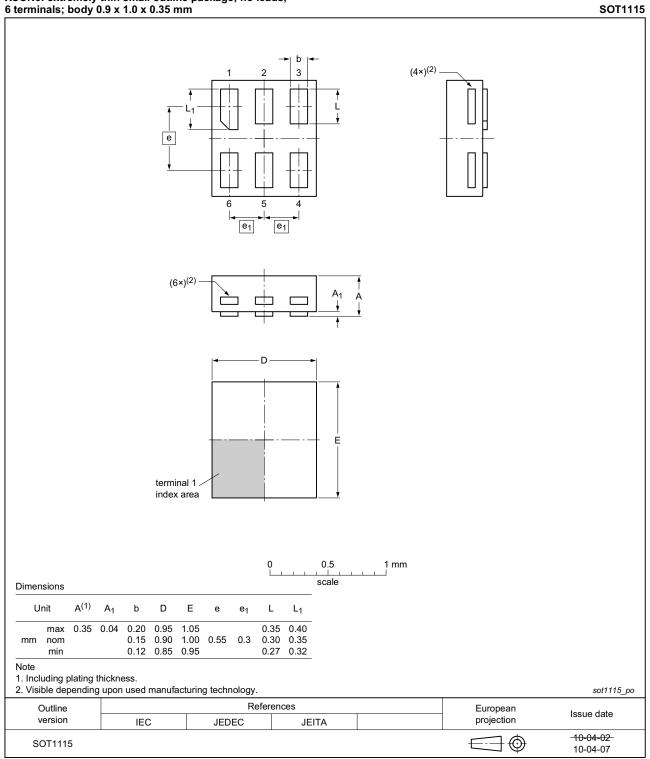


Fig 13. Package outline SOT891 (XSON6)

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Low-power buffer/line driver; 3-state



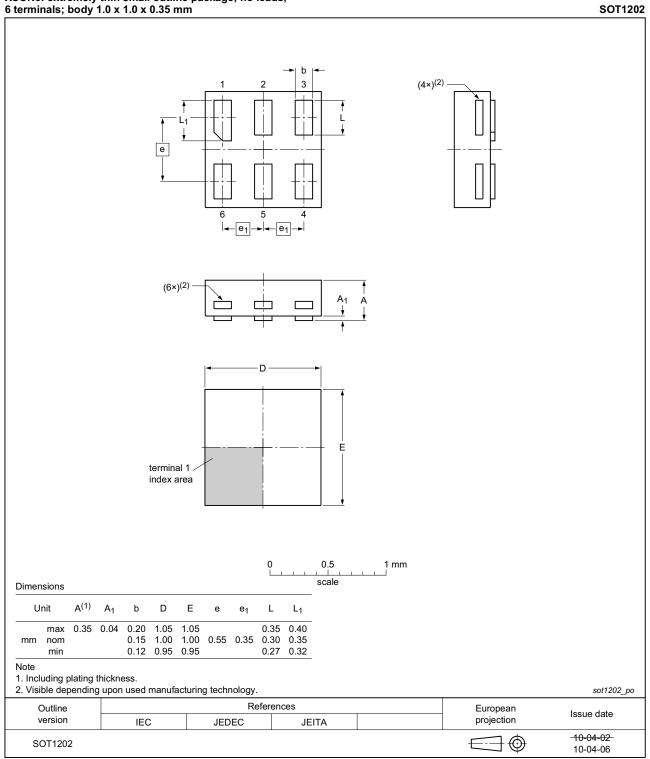
# XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 14. Package outline SOT1115 (XSON6)

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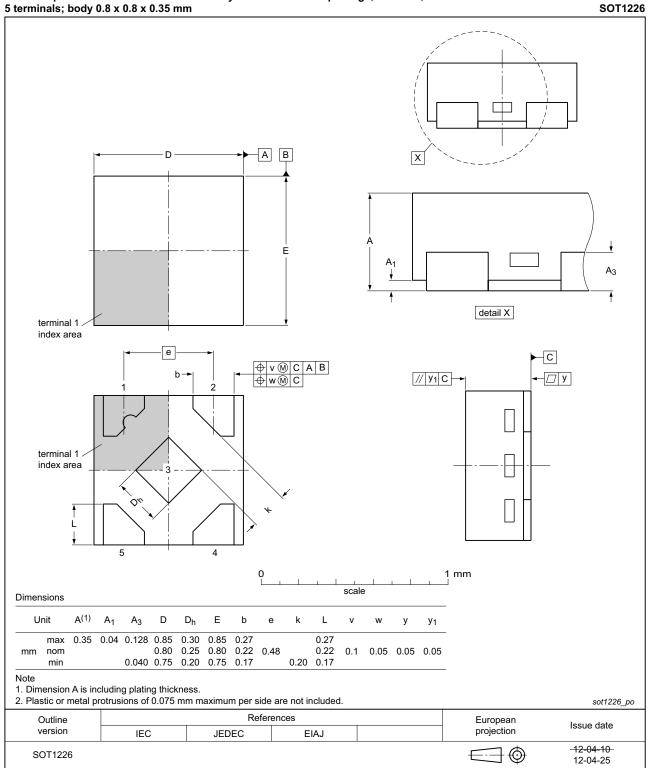


XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 15. Package outline SOT1202 (XSON6)

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Low-power buffer/line driver; 3-state



## X2SON5: plastic thermal enhanced extremely thin small outline package; no leads;

Fig 16. Package outline SOT1226 (X2SON5)

Low-power buffer/line driver; 3-state

### 14. Abbreviations

Acronym CDM	Description Charged Device Model		
CDM	Charged Device Model		
	-		
DUT	Device Under Test		
ESD	ElectroStatic Discharge		
HBM	Human Body Model		
MM	Machine Model		

## **15. Revision history**

#### Table 14. Revision history **Document ID Release date** Data sheet status **Change notice** Supersedes 74AUP1G126 v.6 20151002 Product data sheet 74AUP1G126 v.5 Modifications: I<sub>OK</sub> minimum changed from -0.5 mA to -50 mA (errata) in Table 5.. 74AUP1G126 v.5 20120628 Product data sheet 74AUP1G126 v.4 Modifications: Added type number 74AUP1G126GX (SOT1226) Package outline drawing of SOT886 (Figure 12) modified. 74AUP1G126 v.4 74AUP1G126 v.3 20111124 Product data sheet -20100903 74AUP1G126 v.2 74AUP1G126 v.3 Product data sheet -74AUP1G126 v.2 Product data sheet 74AUP1G126 v.1 20060628 -74AUP1G126 v.1 Product data sheet 20050725 --

### 16. Legal information

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